

IN THE CLAIMS:

Please amend claim 38 as follows:

1. (Withdrawn) A capacitor comprising:
a first electrode made of a metal;
a second electrode made of a conductor; and
a capacitive insulating film existing between the first and second electrodes,
wherein the first electrode has been doped with impurity atoms that suppress decrease in stiffness of the first electrode at a high temperature.
2. (Withdrawn) The capacitor of Claim 1, wherein the first electrode is made of a platinum noble metal.
3. (Withdrawn) The capacitor of Claim 1, wherein the impurity atoms are hydrogen atoms.
4. (Withdrawn) The capacitor of Claim 1, wherein the first electrode has a thickness of 100 nm or less at the thinnest part thereof.
5. (Withdrawn) The capacitor of Claim 1, wherein the capacitive insulating film is a dielectric film made of an oxide.
6. (Withdrawn) The capacitor of Claim 1, wherein the second electrode has been doped with impurity atoms that suppress decrease in stiffness of the second electrode at a high temperature.
7. (Withdrawn) A capacitor comprising:
a first electrode made of a noble metal or a refractory metal;
a second electrode made of a conductor; and
a capacitive insulating film existing between the first and second electrodes,

wherein the first electrode contains hydrogen.

8. (Withdrawn) The capacitor of Claim 7, wherein the first electrode has a thickness of 100 nm or less at the thinnest part thereof.

9. (Withdrawn) The capacitor of Claim 8, wherein the capacitive insulating film is a dielectric film made of an oxide.

10-37. (Cancelled)

38. (Currently Amended) A method for fabricating a semiconductor device, the method comprising the steps of:

- a) forming a metal lower electrode on a substrate;
- b) annealing the metal lower electrode in a reducing atmosphere that contains impurity atoms;
- c) forming a capacitive ~~insulating~~ dielectric film on the metal lower electrode after the step b); and
- d) forming an upper electrode on the capacitive dielectric film, wherein the impurity atoms are introduced into the metal lower electrode in the step b).

39. (Previously Presented) The method of Claim 38, wherein the impurity atoms are hydrogen atoms.

40. (Previously Presented) The method of Claim 38, wherein the annealing process is performed in an argon atmosphere containing hydrogen.

41. (Previously Presented) The method of Claim 38, further comprising steps of forming an insulating film on the substrate and forming a recess on the insulating film before the step a),

wherein the metal lower electrode is formed in the recess in the step b).

42. (Previously Presented) The method of Claim 40, further comprising steps of forming an insulating film on the substrate and forming a recess in the insulating film before the step a),

wherein the metal lower electrode is formed in the recess in the step b).

43. (Previously Presented) The method of Claim 38, wherein the metal lower electrode has a thickness of 100 nm or less at the thinnest part thereof.

44. (Previously Presented) The method of Claim 38, wherein the capacitive dielectric film is formed in an oxidizing atmosphere in the step c).

45. (Previously Presented) The method of Claim 38, further comprising a step of crystallizing the capacitive dielectric film by a heat treatment after the step c) and before the step d).

46. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is made of a noble metal.

47. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is made of a refractory metal.

48. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Pt.

49. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Ir.

50. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Ru.

51. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Rh.

52. (Previously Presented) The method of Claim 38, wherein the capacitive dielectric film is an insulating film made of an oxide.

53. (Previously Presented) The method of Claim 38, wherein the capacitive-dielectric film is composed of BST.

54. (Previously Presented) The method of Claim 38, wherein the capacitive dielectric film is composed of SBT.

55. (Previously Presented) The method of Claim 38, wherein the capacitive dielectric film is composed of PZT.

56. (Previously Presented) The method of Claim 38, wherein the capacitive dielectric film is composed of Ta₂O₅.

57. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Ru and the capacitive dielectric film is composed of Ta₂O₅.

58. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Ir and the capacitive dielectric film is composed of SBT.

59. (Previously Presented) The method of Claim 38, wherein the metal lower electrode is composed of Ir and the capacitive dielectric film is composed of PZT.

60. (Previously Presented) The method of claim 38, wherein the annealing process is performed at the temperature of 450 - 500°C.